TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH595FK

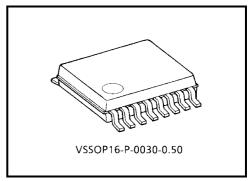
8-Bit Shift Register/Latch (3-State)

The TC7MH595FK is an advanced high speed 8 bit shift register/latch fabricated with silicon gate $\rm C^2MOS$ technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

The TC7MH595FK contains an 8 bit static shift register which feeds an 8 bit storage register.

Shift operation is accomplished on the positive going transition of the SCK input. The output register is loaded with the contents of the shift register on the positive going transition of the RCK input. Since RCK and SCK signals are independent, parallel outputs can be held stable during the shift operation. And, since the parallel outputs are 3-state, it can be directly connected to 8 bit bus. This register can be used in serial-to-parallel conversion, data receivers, etc.



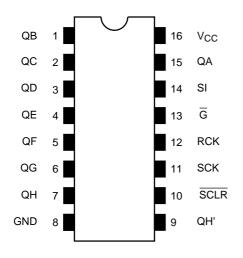
Weight: 0.02 g (typ.)

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

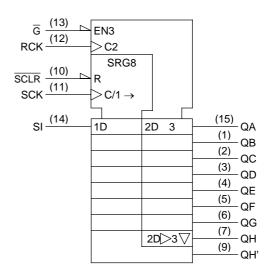
Features

- High speed: $f_{max} = 185 \text{ MHz}$ (typ.) (VCC = 5 V)
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- · Power down protection is provided on all inputs.
- Balanced propagation delays: $t_pLH \approx t_pHL$
- Wide operating voltage range: $V_{CC (opr)} = 2 \sim 5.5 \text{ V}$
- Low noise: VOLP = 1.0 V (max)
- Pin and function compatible with 74ALS595

Pin Assignment (top view)



IEC Logic Symbol

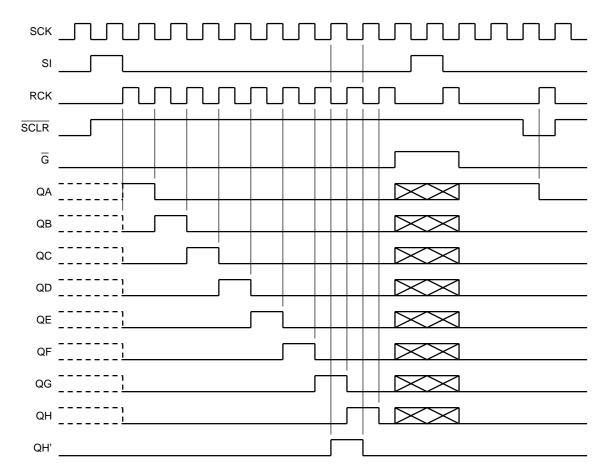


Truth Table

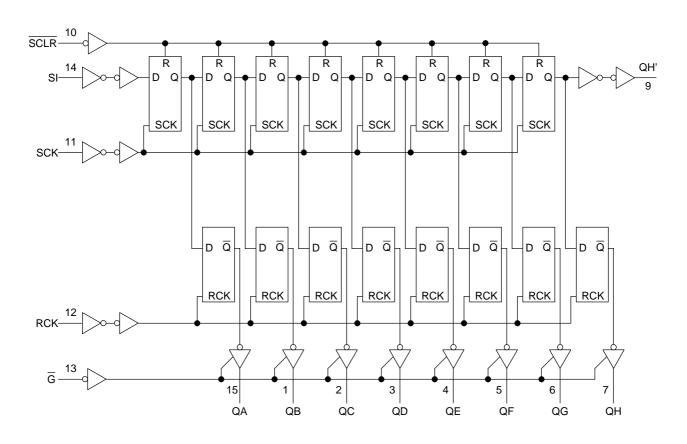
	Inputs				Function			
SI	SCK	SCLR	RCK	G	Function			
Х	Х	Х	Х	Н	QA thru QH outputs disable			
Х	Х	Х	Х	L	QA thru QH outputs enable			
Х	Х	L	Х	Х	Shift register is cleared.			
L		Н	Х	Х	First stage of S.R. becomes "L". Other stages store the data of previous stage, respectively.			
Н		Н	Х	Х	First stage of S.R. becomes "H". Other stages store the data of previous stage, respectively.			
Х	\rightarrow	Н	Х	Х	State of S.R. is not changed.			
Х	Х	Х	 	Х	S.R. data is stored into storage register.			
Х	Х	Х		Х	Storage register stage is not changed.			

X: Don't care

Timing Chart



System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0 \sim 100 \; (V_{CC} = 3.3 \pm 0.3 \; V)$	ns/V
Imput nse and rail time	ui/uv	$0 \sim 20 \; (V_{CC} = 5 \pm 0.5 \; V)$	113/ V

TC7MH595FK

Electrical Characteristics

DC Characteristics

Charac	Symbol	Test Condition			-	Га = 25°(Ta = -40~85°C		Unit	
Ondiactoristics				Symbol	V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
Input voltage			_		2.0	1.50			1.50	_	V
	High level	V _{IH}			3.0~5.5	V _{CC} × 0.7			V _{CC} × 0.7		
Input voltage					2.0			0.50	_	0.50	v
	Low level	V_{IL}	_		3.0~5.5			$\begin{array}{c} V_{CC} \\ \times \ 0.3 \end{array}$	_	V _{CC} × 0.3	
				$I_{OH} = -50 \mu A$	2.0	1.9	2.0	_	1.9	_	V
					3.0	2.9	3.0		2.9	_	
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}		4.5	4.4	4.5		4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58		_	2.48	_	
Output				$I_{OH} = -8 \text{ mA}$	4.5	3.94			3.80	_	
voltage	Low level			I _{OL} = 50 μA	2.0		0	0.1	_	0.1	
					3.0	_	0	0.1	—	0.1	
		V_{OL}	V _{IN} = V _{IH} or V _{IL}		4.5		0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0			0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5			0.36	_	0.44	
3-state output off-state current		I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		5.5	_		±0.25		±2.50	μА
Input leakage	current	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μΑ
Quiescent supp	ply current	Icc	$V_{IN} = V_{CC}$	or GND	5.5			4.0	—	40.0	μΑ

Timing Requirements (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = -40~85°C	Unit	
Characteristics	Symbol	rest Condition	V _{CC} (V)	Тур.	Limit	Limit	Offic	
Minimum pulse width	()		3.3 ± 0.3	_	5.0	5.0	ns	
(SCK, RCK)	t _{w (L)}	_	5.0 ± 0.5	_	5.0	5.0	115	
Minimum pulse width	t (1)		3.3 ± 0.3	_	5.0	5.0	nc	
(SCLR)	t _{w (L)}	_	5.0 ± 0.5	_	5.0	5.0	ns	
Minimum set-up time			3.3 ± 0.3	_	3.5	3.5	no	
(SI-SCK)	t _S	_	5.0 ± 0.5	_	3.0	3.0	ns	
Minimum set-up time	+		3.3 ± 0.3	_	8.0	8.5	ns	
(SCK-RCK)	t _S	_	5.0 ± 0.5	_	5.0	5.0	ns	
Minimum set-up time	ts		3.3 ± 0.3	_	8.0	9.0	no	
(SCLR -RCK)	ι _S	_	5.0 ± 0.5	_	5.0	5.0	ns	
Minimum hold time	4.		3.3 ± 0.3	_	1.5	1.5	no	
(SI-SCK)	t _h	_	5.0 ± 0.5	_	2.0	2.0	ns	
Minimum hold time	+.		3.3 ± 0.3	_	0	0	ns	
(SCK-RCK, SCLR -RCK)	t _h	_	5.0 ± 0.5	_	0	0	115	
Minimum removal time			3.3 ± 0.3	_	3.0	3.0	ns	
(SCLR)	t _{rem}		5.0 ± 0.5	_	2.5	2.5		

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AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -4	Unit	
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
			3.3 ± 0.3	15	_	8.8	13.0	1.0	15.0	- ns
Propagation delay time	t _{pLH}			50	_	11.3	16.5	1.0	18.5	
(SCK-QH')	t _{pHL}	_	5.0 ± 0.5	15	_	6.2	8.2	1.0	9.4	
			3.0 ± 0.3	50	_	7.7	10.2	1.0	11.4	
			3.3 ± 0.3	15		8.4	12.8	1.0	13.7	
Propagation delay time	+		3.3 ± 0.3	50	_	10.9	16.3	1.0	17.2	ns
(SCLR -QH')	t _{pHL}	_	5.0 ± 0.5	15	_	5.9	8.0	1.0	9.1	115
			5.0 ± 0.5	50	_	7.4	10.0	1.0	11.1	
		_	3.3 ± 0.3	15	_	7.7	11.9	1.0	13.5	- ns
Propagation delay time	^t pLH ^t pHL			50	_	10.2	15.4	1.0	17.0	
(RCK-Q _n)			5.0 ± 0.5	15	_	5.4	7.4	1.0	8.5	
				50	_	6.9	9.4	1.0	10.5	
	t _{pZL}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15	_	7.5	11.5	1.0	13.5	- ns
Output enable time				50	_	9.0	15.0	1.0	17.0	
Output enable time			5.0 ± 0.5	15	_	4.8	8.6	1.0	10.0	
				50	_	8.3	10.6	1.0	12.0	
Output disable time	t _{pLZ}	$R_{I} = 1 k\Omega$	3.3 ± 0.3	50	_	12.1	15.7	1.0	16.2	ns
Output disable time	t _{pHZ}		5.0 ± 0.5	50	_	7.6	10.3	1.0	11.0	115
			3.3 ± 0.3	15	80	150	_	70		- MHz
Maximum clock frequency	f		3.3 ± 0.3	50	55	130		50	_	
Maximum clock frequency	f _{max}	_	5.0 ± 0.5	15	135	185	_	115	_	
			J.U ± 0.5	50	95	155	_	85	_	
Input capacitance	C _{IN}	-				4	10	_	10	pF
Output capacitance	C _{OUT}	-	_			6	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note)	_	87	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

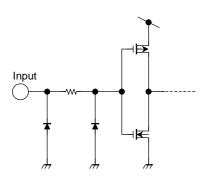
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

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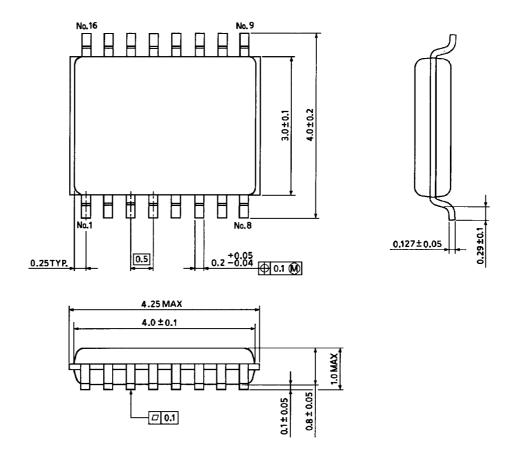
Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		- Unit
Granacieristics	Symbol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.8	1.0	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.8	-1.0	V
Minimum high level dynamic input voltage VIH	V_{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage VIL	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

Input Equivalent Circuit



Package Dimensions



Weight: 0.02 g (typ.)

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